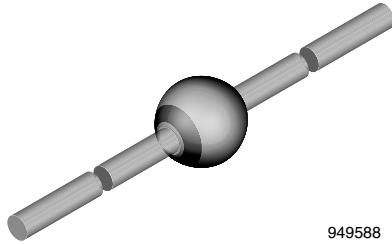




Ultra-Fast Avalanche Sinterglass Diode



949588

FEATURES

- Glass passivated
- Hermetically sealed axial leaded glass envelope
- Low reverse current
- High reverse voltage
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

MECHANICAL DATA

Case: SOD-64

Terminals: plated axial leads, solderable per MIL-STD-750, method 2026

Polarity: color band denotes cathode end

Mounting position: any

Weight: approx. 858 mg

APPLICATIONS

- Switched mode power supplies
- High-frequency inverter circuits

PARTS TABLE		
PART	TYPE DIFFERENTIATION	PACKAGE
SF5400	$V_R = 50\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5401	$V_R = 100\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5402	$V_R = 200\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5403	$V_R = 300\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5404	$V_R = 400\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5405	$V_R = 500\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5406	$V_R = 600\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5407	$V_R = 800\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64
SF5408	$V_R = 1000\text{ V}; I_{FAV} = 3\text{ A}$	SOD-64

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified)					
PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
Reverse voltage = repetitive peak reverse voltage	See electrical characteristics	SF5400	$V_R = V_{RRM}$	50	V
		SF5401	$V_R = V_{RRM}$	100	V
		SF5402	$V_R = V_{RRM}$	200	V
		SF5403	$V_R = V_{RRM}$	300	V
		SF5404	$V_R = V_{RRM}$	400	V
		SF5405	$V_R = V_{RRM}$	500	V
		SF5406	$V_R = V_{RRM}$	600	V
		SF5407	$V_R = V_{RRM}$	800	V
		SF5408	$V_R = V_{RRM}$	1000	V
Peak forward surge current	$t_p = 10\text{ ms}$, half sine wave		I_{FSM}	150	A
Average forward current			I_{FAV}	3	A
Junction and storage temperature range			$T_j = T_{stg}$	- 55 to + 175	$^\circ\text{C}$
Non repetitive reverse avalanche energy	$I_{(BR)R} = 0.4\text{ A}$		E_R	10	mJ

MAXIMUM THERMAL RESISTANCE ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction ambient	Lead length $l = 10\text{ mm}$, $T_L = \text{constant}$	R_{thJA}	25	K/W
	On PC board with spacing 25 mm	R_{thJA}	70	K/W

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 3\text{ A}$	SF5400	V_F	-	-	1.1	V
		SF5401	V_F	-	-	1.1	V
		SF5402	V_F	-	-	1.1	V
		SF5403	V_F	-	-	1.1	V
		SF5404	V_F	-	-	1.1	V
		SF5405	V_F	-	-	1.7	V
		SF5406	V_F	-	-	1.7	V
		SF5407	V_F	-	-	1.7	V
Reverse current	$V_R = V_{RRM}$		I_R	-	-	5	μA
	$V_R = V_{RRM}$, $T_j = 125\text{ }^{\circ}\text{C}$		I_R	-	-	50	μA
Reverse breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	SF5400	$V(\text{BR})_R$	60	-	-	V
		SF5401	$V(\text{BR})_R$	110	-	-	V
		SF5402	$V(\text{BR})_R$	220	-	-	V
		SF5403	$V(\text{BR})_R$	330	-	-	V
		SF5404	$V(\text{BR})_R$	440	-	-	V
		SF5405	$V(\text{BR})_R$	550	-	-	V
		SF5406	$V(\text{BR})_R$	660	-	-	V
		SF5407	$V(\text{BR})_R$	880	-	-	V
Reverse recovery time	$I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $i_R = 0.25\text{ A}$	SF5400	t_{rr}	-	-	50	ns
		SF5401	t_{rr}	-	-	50	ns
		SF5402	t_{rr}	-	-	50	ns
		SF5403	t_{rr}	-	-	50	ns
		SF5404	t_{rr}	-	-	50	ns
		SF5405	t_{rr}	-	-	75	ns
		SF5406	t_{rr}	-	-	75	ns
		SF5407	t_{rr}	-	-	75	ns

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

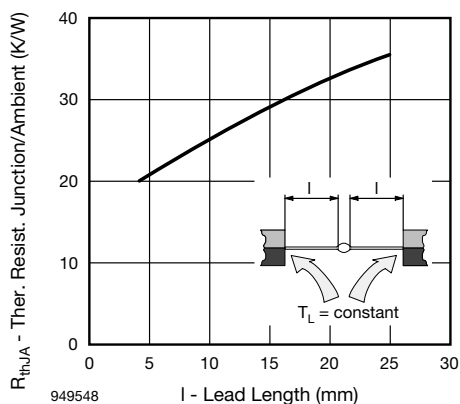


Fig. 1 - Max. Thermal Resistance vs. Lead Length

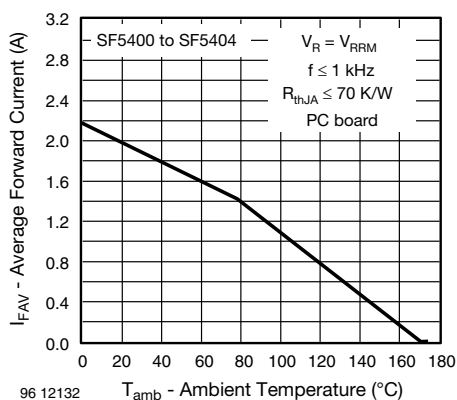


Fig. 2 - Max. Average Forward Current vs. Ambient Temperature



SF5400, SF5401, SF5402, SF5403, SF5404, SF5405, SF5406, SF5407, SF5408

Ultra-Fast Avalanche Sinterglass Diode Vishay Semiconductors

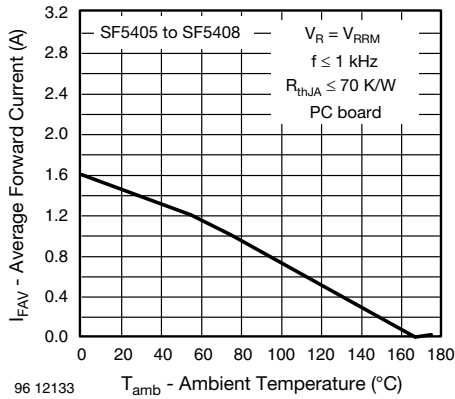


Fig. 3 - Max. Average Forward Current vs. Ambient Temperature

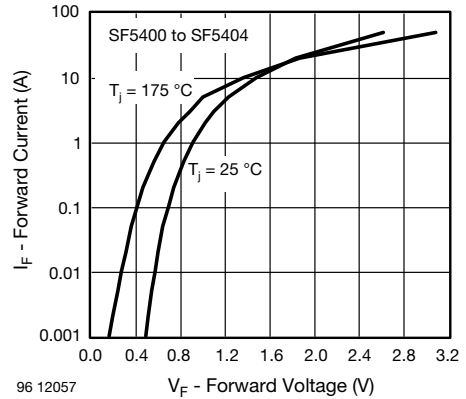


Fig. 6 - Max. Forward Current vs. Forward Voltage

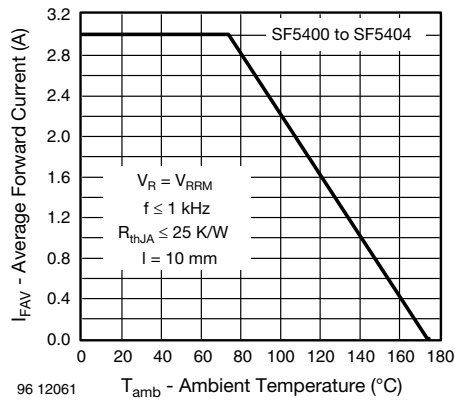


Fig. 4 - Max. Average Forward Current vs. Ambient Temperature

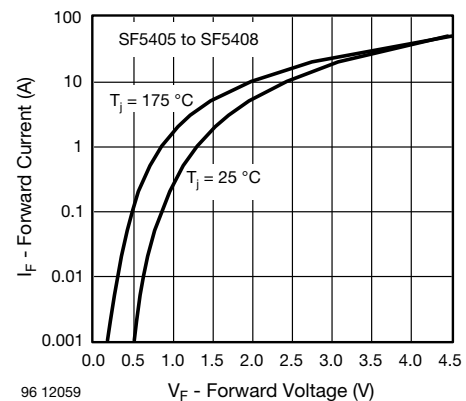


Fig. 7 - Max. Forward Current vs. Forward Voltage

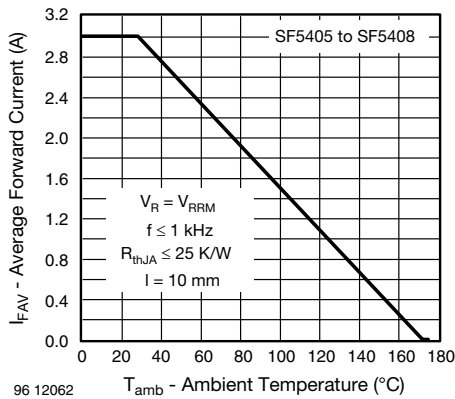


Fig. 5 - Max. Average Forward Current vs. Ambient Temperature

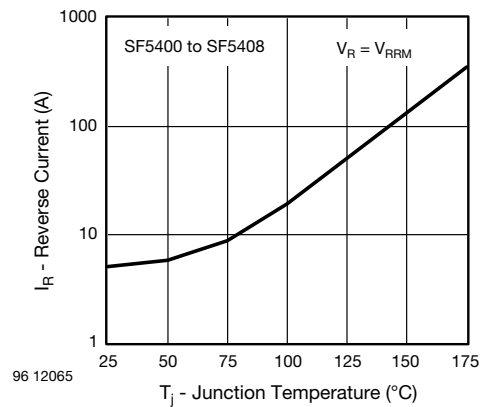


Fig. 8 - Max. Reverse Current vs. Junction Temperature

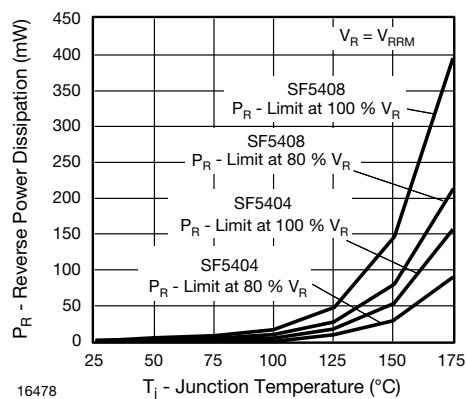


Fig. 9 - Max. Reverse Power Dissipation vs. Junction Temperature

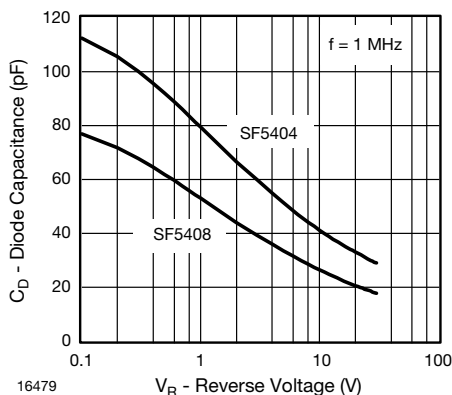
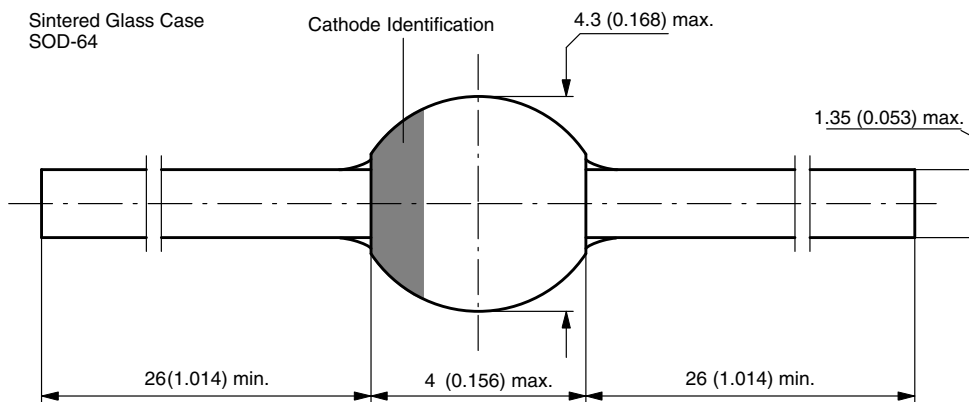


Fig. 10 - Diode Capacitance vs. Reverse Voltage

PACKAGE DIMENSIONS in millimeters (inches): **SOD-64**



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